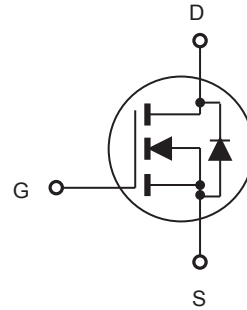
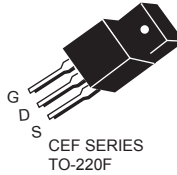


## N-Channel Enhancement Mode Field Effect Transistor

### FEATURES

Type	V <sub>DSS</sub>	R <sub>DS(ON)</sub>	I <sub>D</sub>	@V <sub>GS</sub>
CEP02N6G	600V	5Ω	2.2A	10V
CEB02N6G	600V	5Ω	2.2A	10V
CEF02N6G	600V	5Ω	2.2A <sup>d</sup>	10V

- Super high dense cell design for extremely low R<sub>DS(ON)</sub>.
- High power and current handling capability.
- Lead free product is acquired.



### ABSOLUTE MAXIMUM RATINGS $T_C = 25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Limit		Units
		TO-220/263	TO-220F	
Drain-Source Voltage	V <sub>DS</sub>	600		V
Gate-Source Voltage	V <sub>GS</sub>	±30		V
Drain Current-Continuous @ T <sub>C</sub> = 25 °C @ T <sub>C</sub> = 100 °C	I <sub>D</sub>	2.2	2.2 <sup>d</sup>	A
		1.4	1.4 <sup>d</sup>	A
Drain Current-Pulsed <sup>a</sup>	I <sub>DM</sub> <sup>e</sup>	8.8	8.8 <sup>d</sup>	A
Maximum Power Dissipation @ T <sub>C</sub> = 25 °C - Derate above 25 °C	P <sub>D</sub>	60	33	W
		0.48	0.26	W/°C
Single Pulsed Avalanche Energy <sup>g</sup>	E <sub>AS</sub>	11.25		mJ
Single Pulsed Avalanche Current <sup>g</sup>	I <sub>AS</sub>	1.5		A
Operating and Store Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to 150		°C

### Thermal Characteristics

Parameter	Symbol	Limit		Units
Thermal Resistance, Junction-to-Case	R <sub>θJC</sub>	2.1	3.8	°C/W
Thermal Resistance, Junction-to-Ambient	R <sub>θJA</sub>	62.5	65	°C/W



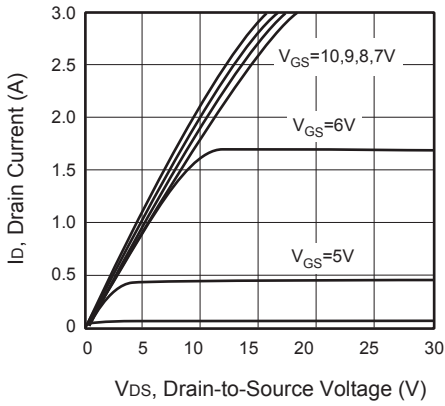
# CEP02N6G/CEB02N6G CEF02N6G

## Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

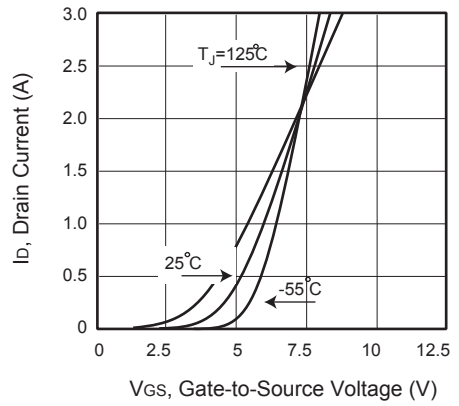
Parameter	Symbol	Test Condition	Min	Typ	Max	Units
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	600			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 600V, V_{GS} = 0V$			25	$\mu A$
Gate Body Leakage Current, Forward	$I_{GSSF}$	$V_{GS} = 30V, V_{DS} = 0V$			100	nA
Gate Body Leakage Current, Reverse	$I_{GSSR}$	$V_{GS} = -30V, V_{DS} = 0V$			-100	nA
<b>On Characteristics<sup>b</sup></b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS} = V_{DS}, I_D = 250\mu A$	2		4	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 1A$		3.8	5	$\Omega$
<b>Dynamic Characteristics<sup>c</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 25V, V_{GS} = 0V,$ $f = 1.0\text{ MHz}$		290		pF
Output Capacitance	$C_{oss}$			70		pF
Reverse Transfer Capacitance	$C_{rss}$			15		pF
<b>Switching Characteristics<sup>c</sup></b>						
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 300V, I_D = 1A,$ $V_{GS} = 10V, R_{GEN} = 18\Omega$		18	36	ns
Turn-On Rise Time	$t_r$			10	20	ns
Turn-Off Delay Time	$t_{d(off)}$			28	56	ns
Turn-Off Fall Time	$t_f$			10	20	ns
Total Gate Charge	$Q_g$	$V_{DS} = 480V, I_D = 1A,$ $V_{GS} = 10V$		6.8	9	nC
Gate-Source Charge	$Q_{gs}$			1.4		nC
Gate-Drain Charge	$Q_{gd}$			3.1		nC
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
Drain-Source Diode Forward Current	$I_S^f$				2	A
Drain-Source Diode Forward Voltage <sup>b</sup>	$V_{SD}$	$V_{GS} = 0V, I_S = 1A$			1.5	V
<b>Notes :</b> □ a.Repetitive Rating : Pulse width limited by maximum junction temperature . b.Pulse Test : Pulse Width $\leq 300\mu s$ , Duty Cycle $\leq 2\%$ . □ c.Guaranteed by design, not subject to production testing. □ d.Limited only by maximum temperature allowed . e.Pulse width limited by safe operating area . f.Full package $I_{S(max)} = 1.5A$ . g.L = 10mH, $I_{AS} = 1.5A$ , $V_{DD} = 50V$ , $R_G = 25\Omega$ , Starting $T_J = 25\text{ C}$						



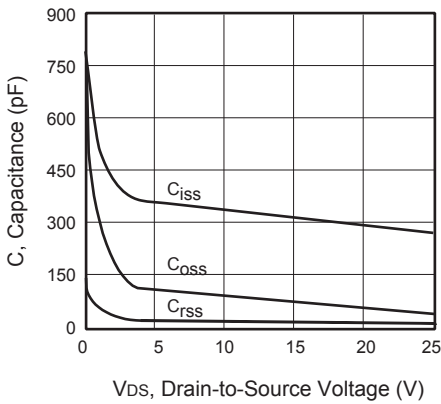
# CEP02N6G/CEB02N6G CEF02N6G



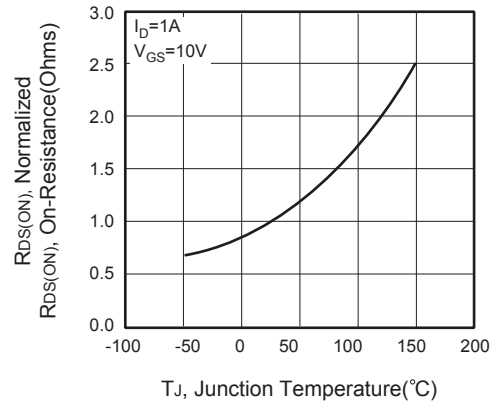
**Figure 1. Output Characteristics**



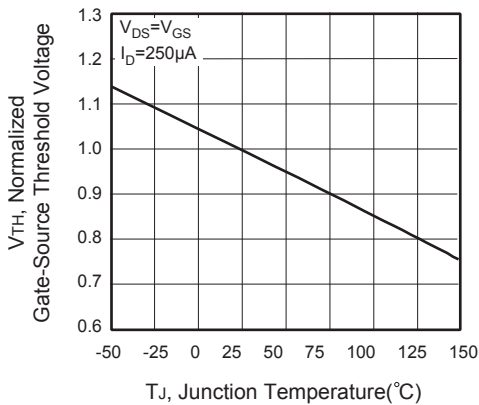
**Figure 2. Transfer Characteristics**



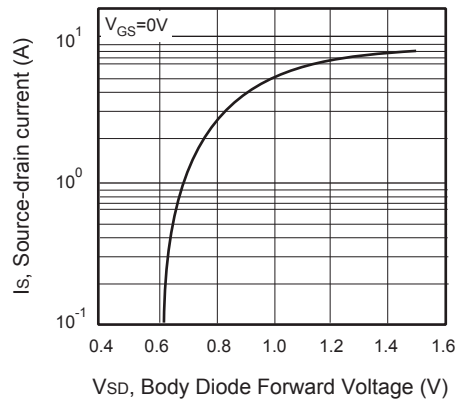
**Figure 3. Capacitance**



**Figure 4. On-Resistance Variation with Temperature**



**Figure 5. Gate Threshold Variation with Temperature**



**Figure 6. Body Diode Forward Voltage Variation with Source Current**

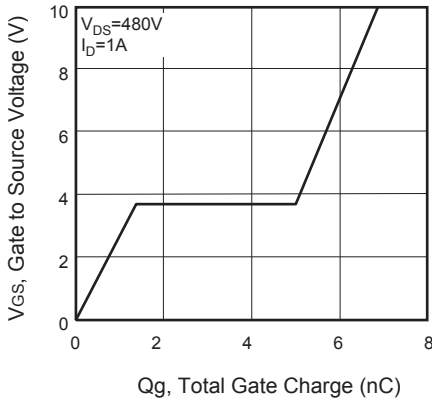


Figure 7. Gate Charge

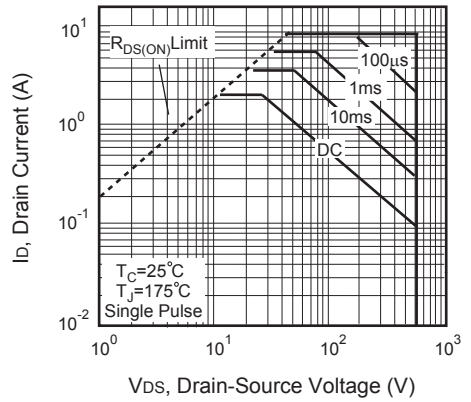


Figure 8. Maximum Safe Operating Area

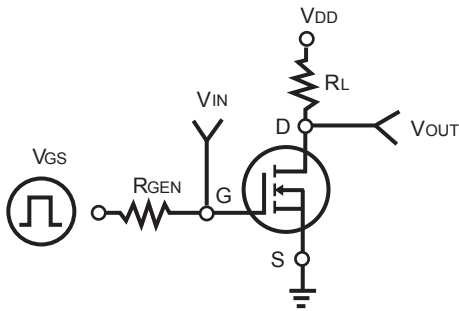


Figure 9. Switching Test Circuit

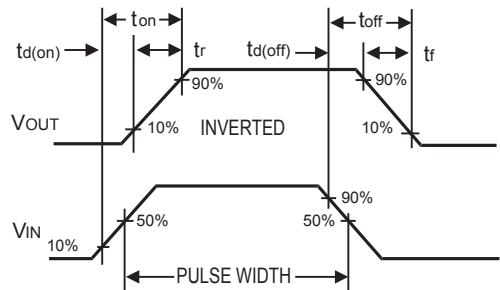


Figure 10. Switching Waveforms

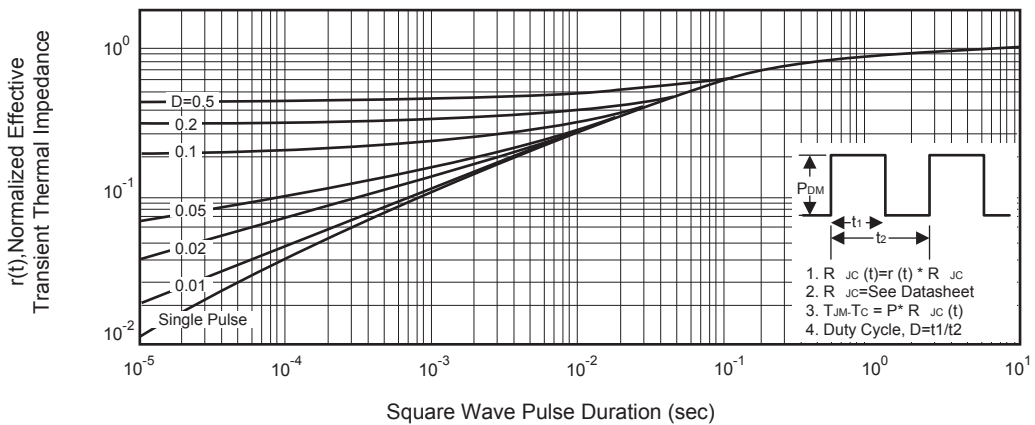


Figure 11. Normalized Thermal Transient Impedance Curve